74LVC1G38

2-input NAND gate; open drain Rev. 7 — 4 October 2012

Product data sheet

1. **General description**

The 74LVC1G38 provides a 2-input NAND function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device as translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Open drain outputs
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from –40 °C to +125 °C.



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3. Ordering information

Table 1. Ordering information

Type number	Package						
	Temperature range Name		Description	Version			
74LVC1G38GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1			
74LVC1G38GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753			
74LVC1G38GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886			
74LVC1G38GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891			
74LVC1G38GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 \times 1.0 \times 0.35 mm	SOT1115			
74LVC1G38GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm	SOT1202			
74LVC1G38GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226			

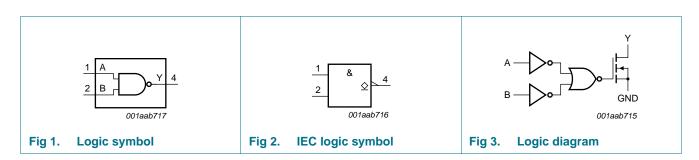
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74LVC1G38GW	YB
74LVC1G38GV	YB
74LVC1G38GM	YB
74LVC1G38GF	YB
74LVC1G38GN	YB
74LVC1G38GS	YB
74LVC1G38GX	YB

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



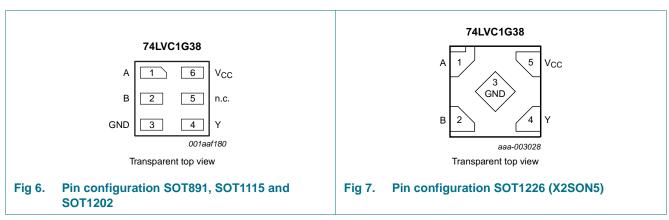
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6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description	
	TSSOP5 and X2SON5	XSON6	
Α	1	1	data input
В	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
V_{CC}	5	6	supply voltage

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7. Functional description

Table 4. Function table[1]

Input		Output
Α	В	Υ
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

^[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF state

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V_{I}	input voltage		<u>[1]</u> -0.5	+6.5	V
I _{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0 V$	-	±50	mA
V _O	output voltage	Active mode	[1][2] -0.5	+6.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[3]</u> _	300	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 and X2SON 5packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	5.5	V
		Disable mode; $V_{CC} = 1.65 \text{ V}$ to 5.5 V	0	-	5.5	V
		Power-down mode; V _{CC} = 0 V	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C[1]					
V_{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}	-	-	-	
		I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.3	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	μА
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	±0.1	±10	μА
l _{OFF}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	±0.1	±10	μΑ
I _{CC}	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	0.1	10	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V} \text{ to } 5.5 \text{ V}; \text{ per pin}$	-	5	500	μΑ
Cı	input capacitance		-	2.5	-	pF

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 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}	-	-	-	
		I_O = 100 $\mu A;V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	٧
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	٧
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
l _l	input leakage current	$V_1 = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±100	μΑ
loz	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±200	μА
OFF	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	±200	μΑ
lcc	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	-	200	μА
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V} \text{ to } 5.5 \text{ V}; \text{ per pin}$	-	-	5000	μА

^[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

2-input NAND gate; open drain

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 9.

Symbol	Parameter	Conditions		-40 °C to +85 °C			-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	A, B to Y; see Figure 8	2]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	3.0	10.0	1.0	12.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.5	1.8	6.0	0.5	7.5	ns
		V _{CC} = 2.7 V		0.5	2.5	5.0	0.5	6.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.5	2.3	4.5	0.5	5.7	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.5	3.9	0.5	4.9	ns
C _{PD}	power dissipation capacitance	$V_{CC} = 3.3 \text{ V};$ $V_I = \text{GND to } V_{CC}$	3]	-	6	-	-	-	pF

^[1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.8$ V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

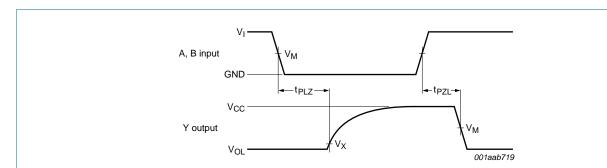
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = sum of outputs.$

12. AC waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

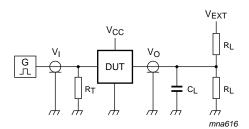
Fig 8. The input (A, B) to output (Y) propagation delays.

^[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

2-input NAND gate; open drain

Table 9. Measurement points

Supply voltage	Input	Output		
V _{CC}	V _M	V _M	V _X	
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V	
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V	



Test data is given in Table 10.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

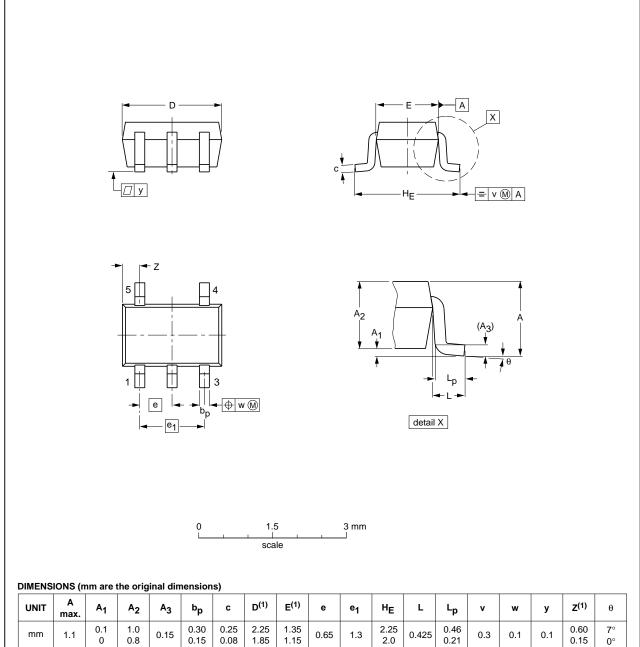
Supply voltage	Input	Input		Load		
V _{CC}	V _I	t _r , t _f	CL	R _L	t _{PLH} , t _{PHL}	
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	open	
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	

2-input NAND gate; open drain

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



mm

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

0.15

0.08

1.85

OUTLINE		REFER	REFERENCES		EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A			-00-09-01- 03-02-19

Fig 10. Package outline SOT353-1 (TSSOP5)

8.0

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Plastic surface-mounted package; 5 leads

SOT753

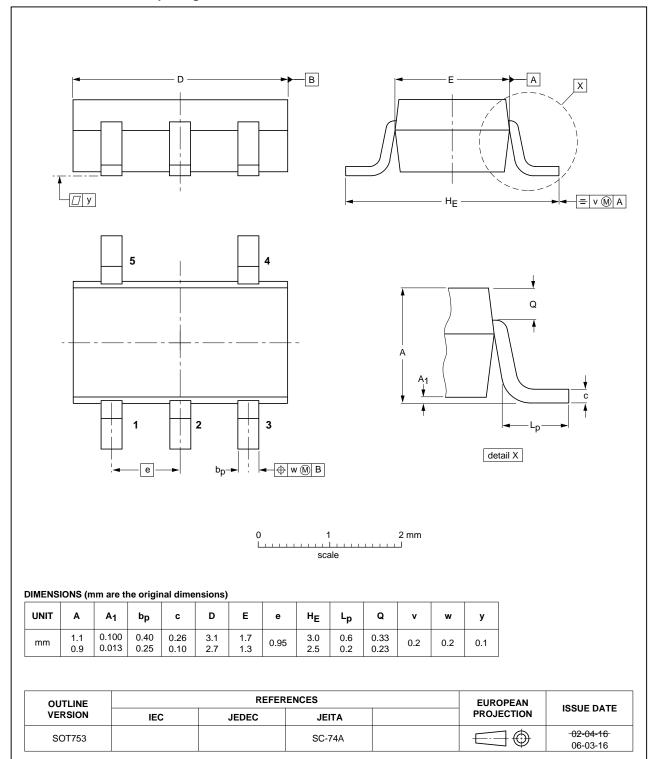


Fig 11. Package outline SOT753 (SC-74A)

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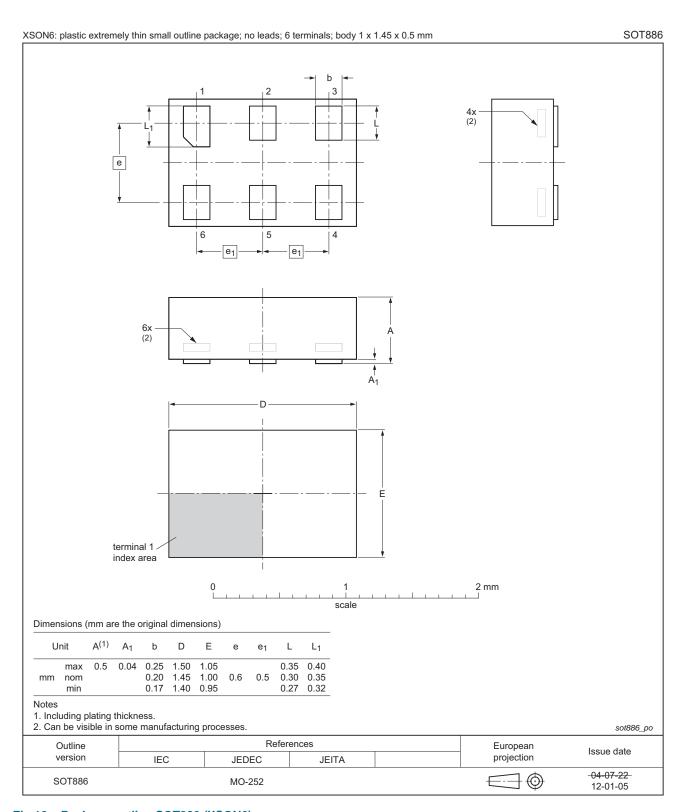


Fig 12. Package outline SOT886 (XSON6)

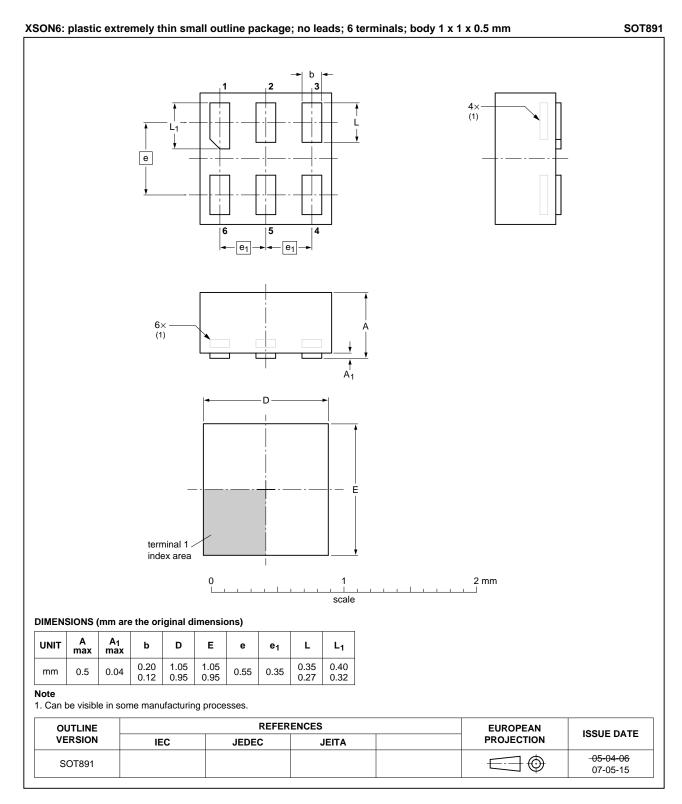


Fig 13. Package outline SOT891 (XSON6)

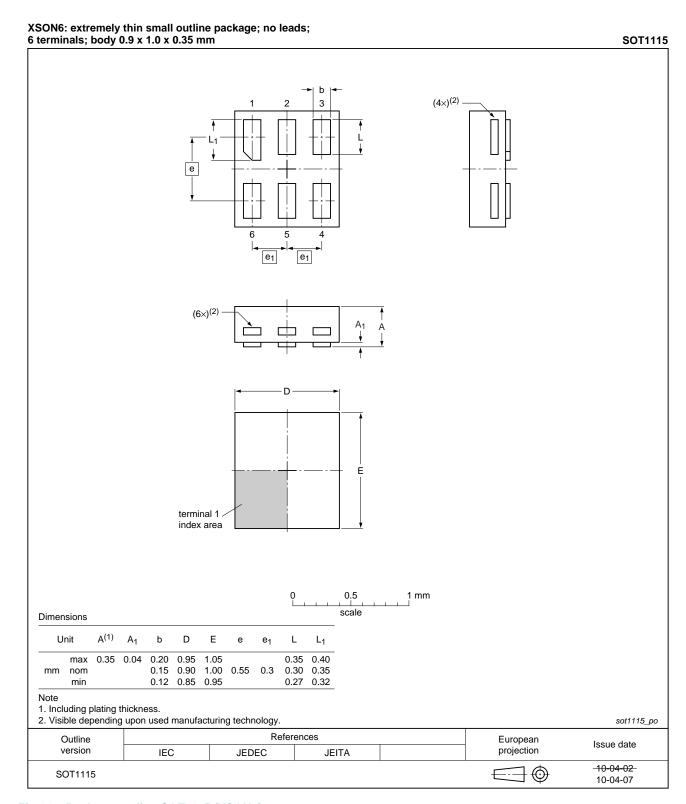


Fig 14. Package outline SOT1115 (XSON6)

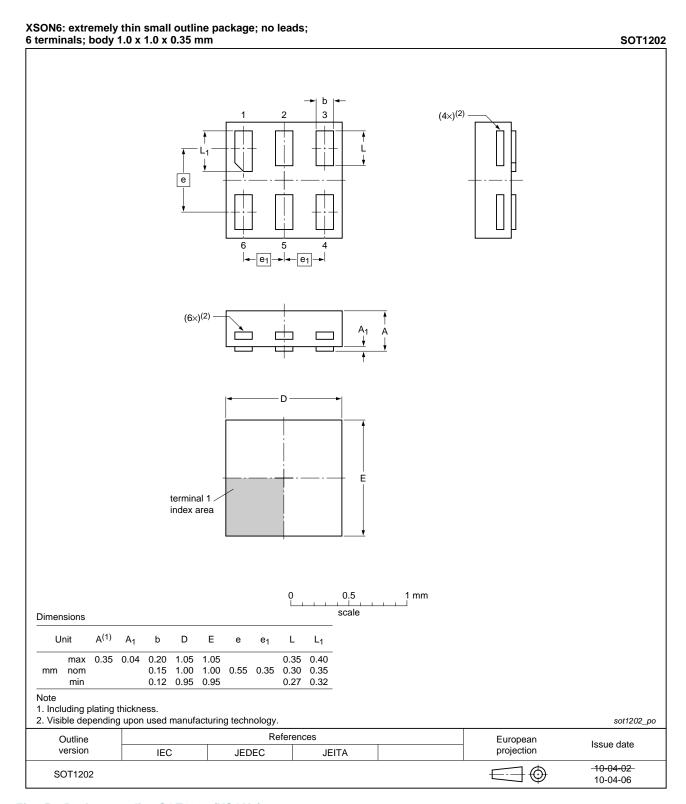


Fig 15. Package outline SOT1202 (XSON6)

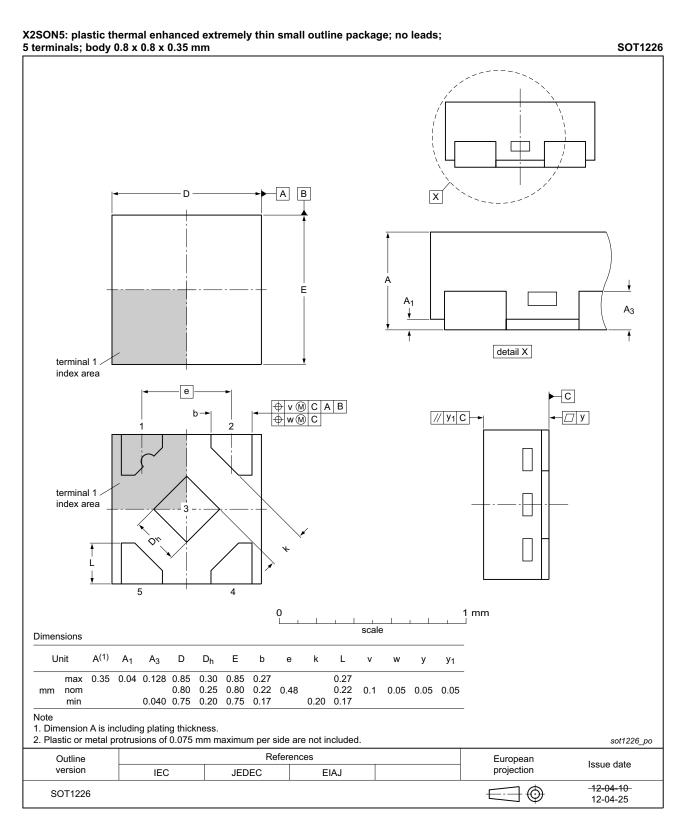


Fig 16. Package outline SOT1226 (X2SON5)

2-input NAND gate; open drain

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74LVC1G38 v.7	20121004	Product data sheet	-	74LVC1G38 v.6		
Modifications:	Pin configuration SOT1226 (Figure 7) modified.					
74LVC1G38 v.6	20120702	Product data sheet	-	74LVC1G38 v.5		
Modifications:	 Added type num 	Added type number 74LVC1G38GX (SOT1226)				
	 Package outline drawing of SOT886 (<u>Figure 12</u>) modified. 					
74LVC1G38 v.5	20111206	Product data sheet	-	74LVC1G38 v.4		
Modifications:	Legal pages updated.					
74LVC1G38 v.4	20101005	Product data sheet	-	74LVC1G38 v.3		
74LVC1G38 v.3	20070827	Product data sheet	-	74LVC1G38 v.2		
74LVC1G38 v.2	20060913	Product data sheet	-	74LVC1G38 v.1		
74LVC1G38 v.1	20041018	Product data sheet	-	-		

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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